Shin-ichiro Gozu

List of Publications by Year
in descending order

80	856	567281 15	526287 27
papers	citations	h-index	g-index

80	80	80	539
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Large spontaneous spin splitting in gate-controlled two-dimensional electron gases at normal In0.75Ga0.25As/In0.75Al0.25As heterojunctions. Journal of Applied Physics, 2001, 89, 8017-8021.	2.5	183
2	Heteroepitaxial growth of GaSb on Si(001) substrates. Journal of Crystal Growth, 2004, 264, 21-25.	1.5	106
3	Initial growth stage of GaSb on Si(001) substrates with AlSb initiation layers. Journal of Crystal Growth, 2005, 283, 297-302.	1.5	51
4	Over 1.3Î¼m continuous-wave laser emission from InGaSb quantum-dot laser diode fabricated on GaAs substrates. Applied Physics Letters, 2005, 86, 203118.	3.3	42
5	Low Temperature High Electron Mobility in In0.75Ga0.25As/In0.75Al0.25As Modulation-Doped Hetrostructures Grown on GaAs Substrate. Japanese Journal of Applied Physics, 1998, 37, L1501-L1503.	1.5	35
6	Very high electron mobilities at low temperatures in InxGa1â^'xAs/InyAl1â^'yAs HEMTs grown lattice-mismatched on GaAs substrates. Journal of Crystal Growth, 1999, 201-202, 749-752.	1.5	27
7	Strong photoluminescence and laser operation of InAs quantum dots covered by a GaAsSb strain-reducing layer. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 395-399.	2.7	25
8	Cross Phase Modulation Efficiency Enhancement in In_{0.8}Ga_{0.2}As/Al_{0.5}Ga_{0.5}As/AlAs_{0.56}Sb_{0.44}Coupled Double Quantum Wells by Tailoring Interband Transition Wavelength. Applied Physics Express, 0, 2, 042201.	2.4	23
9	Spin-splitting transport in In0.75Ga0.25As/In0.75Al0.25As quantum wire field-effect-transistor. Physica B: Condensed Matter, 1999, 272, 114-116.	2.7	22
10	Study for realization of spin-polarized field effect transistor in In0.75Ga0.25As/In0.75Al0.25As heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 399-402.	2.7	22
11	Large spontaneous spin-splitting and enhanced effective g-factor in two-dimensional electron gases at In0.75Ga0.25As/In0.75Al0.25As metamorphic heterojunctions. Physica B: Condensed Matter, 2001, 298, 65-69.	2.7	20
12	High-Quality GaSb/AlGaSb Quantum Well Grown on Si Substrate. Japanese Journal of Applied Physics, 2005, 44, L15-L17.	1.5	18
13	Study of the shrinkage caused by holographic grating formation in acrylamide based photopolymer film. Optics Express, 2011, 19, 13386.	3.4	16
14	Characterization of high indium content metamorphic InGaAs/InAlAs modulation-doped heterostructures. Journal of Crystal Growth, 2001, 227-228, 155-160.	1.5	15
15	1.5Î¼m emission from InAs quantum dots with InGaAsSb strain-reducing layer grown on GaAs substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 81-84.	2.7	15
16	1.55-Âµm-Waveband Emissions from Sb-Based Quantum-Dot Vertical-Cavity Surface-Emitting Laser Structures Fabricated on GaAs Substrate. Japanese Journal of Applied Physics, 2006, 45, 3423-3426.	1.5	15
17	Growth of InGaSb Quantum Dot Structures on GaAs and Silicon Substrates. Japanese Journal of Applied Physics, 2007, 46, 2401-2404.	1.5	15
18	Band edge tailoring of InGaAs/AlAsSb coupled double quantum wells for a monolithically integrated all-optical switch. Optics Express, 2013, 21, 15840.	3.4	14

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19	Experimental and theoretical study of cross-phase modulation in InGaAs/AlAsSb coupled double quantum wells with a AlGaAs coupling barrier. Physical Review B, 2009, 80, .	3.2	12
20	All-optical control of the resonant-photon tunneling effect observed in GaAsâˆ•AlGaAs multilayered structures containing quantum dots. Applied Physics Letters, 2005, 87, 231119.	3.3	10
21	Determination of Rashba spin splitting in InxGa1âˆ’xAs/InyAl1âˆ’yAs by far-infrared magneto-optical absorption. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 432-434.	2.7	9
22	(In)GaSb/AlGaSb quantum wells grown on Si substrates. Thin Solid Films, 2007, 515, 4467-4470.	1.8	9
23	Crystal quality of InGaAs/AlAs/InAlAs coupled double quantum wells for intersubband transition devices. Journal of Crystal Growth, 2015, 425, 102-105.	1.5	9
24	Growth of InAsSb Quantum Dots on GaAs Substrates Using Periodic Supply Epitaxy. Japanese Journal of Applied Physics, 2005, 44, L696-L698.	1.5	8
25	Simultaneous generation of intersubband absorption and quantum well intermixing through silicon ion implantation in undoped InGaAs/AlAsSb coupled double quantum wells. Applied Physics Letters, 2010, 96, 101901.	3.3	8
26	Ultrafast all-optical switch with cross-phase modulation by area-selective ion implantation in InGaAs/AlAsSb coupled double quantum wells. Optics Express, 2012, 20, B279.	3.4	8
27	InGaAs/AlAs/InAlAs coupled double quantum wells for intersubband transition devices operating at 1550nm. Journal of Crystal Growth, 2013, 378, 134-136.	1.5	7
28	Large and anisotropic zero-field spin-splittings in InxGa1âˆ’xAs/InyAl1âˆ’yAs (x,y>0.6) heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 992-996.	2.7	6
29	Possible large zero-field spin-splittings in InxGa1âˆ’xAs/InyA11âˆ’yAs (x,y=0.75) heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 771-774.	2.7	6
30	Residual carrier density in GaSb grown on Si substrates. Thin Solid Films, 2006, 515, 748-751.	1.8	6
31	Nanoscale structure fabrication of multiple AlGaSbâˆ•InGaSb quantum wells by reactive ion etching with chlorine-based gases toward photonic crystals. Journal of Vacuum Science & Technology B, 2006, 24, 2291.	1.3	6
32	Ultrafast electron dynamics of intersubband excitation concerning cross-phase modulation in an InGaAs/AlAs/AlAsSb coupled double quantum well. Applied Physics Letters, 2011, 98, 251104.	3.3	6
33	Spontaneous spin-splitting observed in resonant tunneling diode with narrow band-gap asymmetric quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 815-818.	2.7	5
34	Optical communications waveband lasing from Sb-based quantum dot vertical-cavity laser. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 516-519.	2.7	5
35	Molecular beam epitaxy of AlAsSb/AlAs/InGaAs coupled double quantum wells with extremely thin AlAs center barrier. Journal of Crystal Growth, 2009, 311, 1700-1702.	1.5	5
36	All-Optical Cross-Phase Modulation Generation by Ion Implantation in IIIâ€“V Quantum Wells. IEEE Photonics Technology Letters, 2010, 22, 1820-1822.	2.5	5

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37	Compensation mechanism of undoped GaAs films grown by molecular beam epitaxy using an As-valved cracker cell. Applied Surface Science, 1998, 130-132, 409-413.	6.1	4
38	An investigation of tunable spinâ€“orbit interactions in front-gated In0.75Ga0.25As/In0.75Al0.25As heterojunctions. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 77-80.	2.7	4
39	Ballistic Spin Transport in Four-Terminal NiFe/In0.75Ga0.25As Structure. Japanese Journal of Applied Physics, 2001, 40, L1093-L1096.	1.5	4
40	Sb-based quantum dots for creating novel light-emitting devices for optical communications. , 2006, , .		4
41	Highly-Ordered and Highly-Stacked (150-Layer) Quantum Dots. , 0, , .		4
42	Refractive index of Si-doped n-InGaAs. Journal of Applied Physics, 2008, 104, 073507.	2.5	4
43	Effects of shutter transients in molecular beam epitaxy. Nanoscale Research Letters, 2012, 7, 620.	5.7	4
44	Critical layer thickness study in In0.75Ga0.25As/In0.5Al0.5As pseudomorphic resonant tunneling diode structure grown on GaAs substrates. Journal of Crystal Growth, 2001, 227-228, 161-166.	1.5	3
45	Change in band configuration of quantum wells from type-II to type-I by increasing Sb composition x. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 230-233.	2.7	3
46	Site control of very low density InAs QDs on patterned GaAs nano-wire surfaces. Journal of Crystal Growth, 2007, 301-302, 846-848.	1.5	3
47	Molecular beam epitaxy and characterization of InGaAsâ^•AlAsâ^•AlAsSb coupled double quantum wells with extremely thin coupling barriers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3C25-C3C28.	1.2	3
48	All-optical XOR logic gate using intersubband transition in III-V quantum well materials. Optics Express, 2014, 22, 12861.	3.4	3
49	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 327-329.	0.5	2
50	Strain control of InGaAs/AlAs/AlAsSb quantum wells by interface termination method between AlAs and AlAsSb. Journal of Crystal Growth, 2011, 323, 39-41.	1.5	2
51	Four-wave mixing in InGaAs/AlAsSb intersubband transition optical waveguides. Journal of Applied Physics, 2011, 110, .	2.5	2
52	Photoreflectance study of InGaAs/AlAsSb coupled double quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 334-337.	0.8	2
53	Residual electric fields of InGaAs/AlAs/AlAsSb (001) coupled double quantum wells structures assessed by photoreflectance anisotropy. International Journal of Modern Physics B, 2016, 30, 1550248.	2.0	2
54	Growth of InAs Quantum Dots on a Low Lattice-Mismatched AlGaSb Layer Prepared on GaAs (001) Substrates. Solid State Phenomena, 2004, 99-100, 49-54.	0.3	1

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55	Metamorphic InGaAs/AlAsSb quantum wells grown on GaAs substrates for intersubband devices operating toward short-wavelength region. Electronics Letters, 2006, 42, 600.	1.0	1
56	Selective Formation of Self-Organized InAs Quantum Dots Grown on Patterned GaAs Substrates by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 3556-3559.	1.5	1
57	Optical Cavity Properties of Metal Mirror Microcavities with InAsSb Quantum Dots. Japanese Journal of Applied Physics, 2006, 45, 8650-8652.	1.5	1
58	High-resolution X-ray diffraction analysis of InGaAs/AlAsSb coupled double quantum wells grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1707-1710.	1.5	1
59	All-optical wavelength conversion at 40Gb/s with enhanced XPM by facet reflection using intersubband transition in InGaAs/AlAsSb quantum well waveguide. , 2010, , .		1
60	Observation of Spin Relaxation in InGaAs/AlAsSb Quantum Wells. Japanese Journal of Applied Physics, 2010, 49, 04DM03.	1.5	1
61	Exciton spin relaxation in In0.53Ga0.47As/AlAs0.56Sb0.44 quantum wells. Applied Physics Letters, 2012, 100, 092401.	3.3	1
62	Bandgap Control for Intersubband Transition in InGaAs/AlAsSb Coupled Double Quantum Wells. IEEE Photonics Technology Letters, 2013, 25, 1474-1477.	2.5	1
63	Dependencies of low-temperature electronic properties of MBE-grown GaAs/AlGaAs single heterojunctions upon arsenic species. Journal of Crystal Growth, 1999, 201-202, 800-804.	1.5	0
64	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 469-472.	0.5	0
65	Growth of antimonide compound semiconductor on Si(001) substrate. , 2006, , .		0
66	Microwave induced Shubnikovâ€“de Hass-type oscillation in InGaAs/InAlAs heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 393-396.	2.7	0
67	Analysis of Novel Alignment Method for Fabricating Three-Dimensional Photonic Crystal. Japanese Journal of Applied Physics, 2006, 45, L135-L137.	1.5	0
68	Strong optical emissions from two-dimensional metal photonic crystals with semiconductor multiple quantum wells. Journal of Applied Physics, 2007, 101, 086107.	2.5	0
69	Large nitrogen composition of GaNSb grown by RF-MBE. AIP Conference Proceedings, 2007, , .	0.4	0
70	Nano-positioning of Sb-based semiconductor quantum structures for novel communications devices. AIP Conference Proceedings, 2007, , .	0.4	0
71	Metamorphic molecular beam epitaxy growth and selective wet etching for epitaxial layer lift-off of AlAsSb toward optical waveguides with high optical confinement. Journal of Crystal Growth, 2007, 301-302, 955-958.	1.5	0
72	Refractive index of high-carrier-doped InGaAs/AlAsSb coupled double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2661-2664.	2.7	0

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73	Carrier spin relaxation in InGaAsâˆ•AlAsSb quantum wells. , 2011, , .		0
74	Surface photovoltage and photoreflectance study of InGaAsâˆ•AlAsSb quantum wells. , 2011, , .		0
75	Optical and structural properties of In[sub 0.64]Ga[sub 0.36]Asâˆ•Al[sub x]Ga[sub 1â^'x]As(xâ‰0.2)âˆ•AlAsSb coupled double quantum wells. , 2013, , .		0
76	Picosecond Carrier Spin Relaxation in In0.8Ga0.2As/AlAs/AlAs0.56Sb0.44Coupled Double Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 04CM05.	1.5	0
77	Highly strained InAlP/InGaAs-based coupled double quantum wells on InP substrates. Japanese Journal of Applied Physics, 2018, 57, 055501.	1.5	0
78	Monolithically Integrated Intersubband All-Optical Switch using Area-Selective Activation of Cross-Phase Modulation in InGaAs/AlAsSb Quantum Wells. , 2012, , .		0
79	Intersubband All-Optical Switch with Bandgap Control of InGaAs/AlAsSb Quantum Wells. , 2013, , .		0
80	Photoluminescence of an InSb layer on a Germanium substrate. Semiconductor Science and Technology, 0, , .	2.0	0